



STS4DNF30L

DUAL N-CHANNEL 30V - 0.039Ω - 4A SO-8

STripFET™ POWER MOSFET

PRELIMINARY DATA

TYPE	V _{DSS}	R _{DS(on)}	I _D
STS4DNF30L	30 V	< 0.050 Ω	4 A

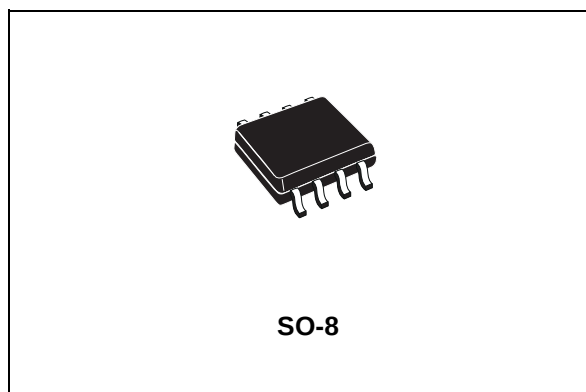
- TYPICAL R_{DS(on)} = 0.039 Ω
- STANDARD OUTLINE FOR EASY AUTOMATED SURFACE MOUNT ASSEMBLY
- LOW THRESHOLD DRIVE

DESCRIPTION

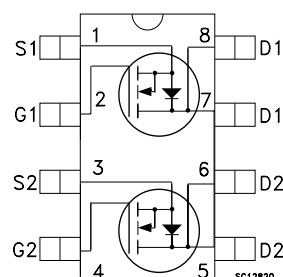
This Power MOSFET is the second generation of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

APPLICATIONS

- BATTERY MANAGMENT IN NOMADIC EQUIPMENT
- POWER MANAGMENT IN CELLULAR PHONES
- DC MOTOR DRIVE



INTERNAL SCHEMATIC DIAGRAM



MOSFET ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	30	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	30	V
V _{GS}	Gate- source Voltage	± 16	V
I _D	Drain Current (continuous) at T _C = 25°C	4	A
I _D	Drain Current (continuous) at T _C = 100°C	2.5	A
I _{DM} (●)	Drain Current (pulsed)	16	A
P _{TOT}	Total Dissipation at T _C = 25°C Dual Operation	2	W

(●) Pulse width limited by safe operating area.

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THERMAL DATA

Rthj-amb	(*)Thermal Resistance Junction-ambient Max	62.5	°C/W
T _{stg}	Storage Temperature Range	-55 to 150	°C
T _J	Junction Temperature	150	°C
(*) Mounted on FR-4 board (t ≤ 10sec)			

MOSFET ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 µA, V _{GS} = 0	30			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125 °C			1 10	µA µA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 16 V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250µA	1			V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V, I _D = 2 A V _{GS} = 4.5V, I _D = 2 A		0.039 0.046	0.050 0.060	Ω Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (1)	Forward Transconductance	V _{DS} > I _{D(on)} × R _{DS(on)} max, I _D = 2 A	1	3		S
C _{iss}	Input Capacitance	V _{DS} = 25V, f = 1 MHz, V _{GS} = 0		330		pF
C _{oss}	Output Capacitance			90		pF
C _{rss}	Reverse Transfer Capacitance			40		pF

ELECTRICAL CHARACTERISTICS (CONTINUED)**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 15\text{ V}$, $I_D = 2\text{ A}$, $R_G = 4.7\Omega$		11		ns
t_r	Rise Time	$V_{GS} = 4.5\text{ V}$ (see test circuit, Figure 3)		100		ns
Q_g	Total Gate Charge	$V_{DD} = 24\text{ V}$, $I_D = 4\text{ A}$, $V_{GS} = 10\text{ V}$		6.5	9	nC
Q_{gs}	Gate-Source Charge			3.6		nC
Q_{gd}	Gate-Drain Charge			2		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off Delay Time	$V_{DD} = 15\text{ V}$, $I_D = 2\text{ A}$, $R_G = 4.7\Omega$, $V_{GS} = 4.5\text{ V}$		25		ns
t_f	Fall Time	(see test circuit, Figure 3)		22		ns
$t_{r(voff)}$	Off-Voltage Rise Time	$V_{DD} = 24\text{ V}$, $I_D = 4\text{ A}$, $R_G = 4.7\Omega$, $V_{GS} = 4.5\text{ V}$		22		ns
t_f	Fall Time	(see test circuit, Figure 5)		55		ns
t_c	Cross-over Time			75		ns

SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				4	A
$I_{SDM(2)}$	Source-drain Current (pulsed)				16	A
$V_{SD(1)}$	Forward On Voltage	$I_{SD} = 4\text{ A}$, $V_{GS} = 0$			1.2	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 4\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 20\text{ V}$, $T_j = 150^\circ\text{C}$		30		ns
Q_{rr}	Reverse Recovery Charge	(see test circuit, Figure 5)		18		nC
I_{RRM}	Reverse Recovery Current			1.2		A

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

2. Pulse width limited by safe operating area.

Fig. 1: Unclamped Inductive Load Test Circuit

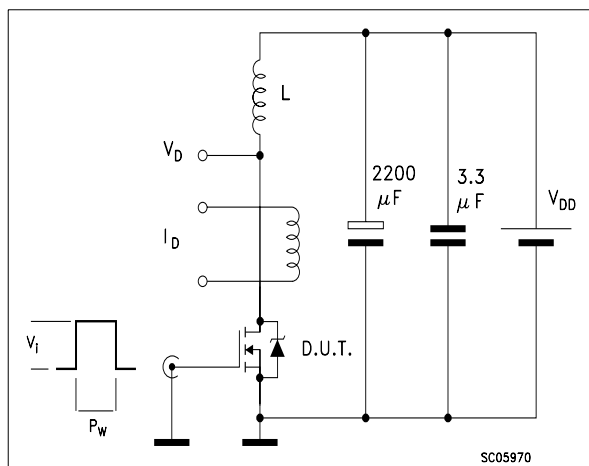


Fig. 2: Unclamped Inductive Waveform

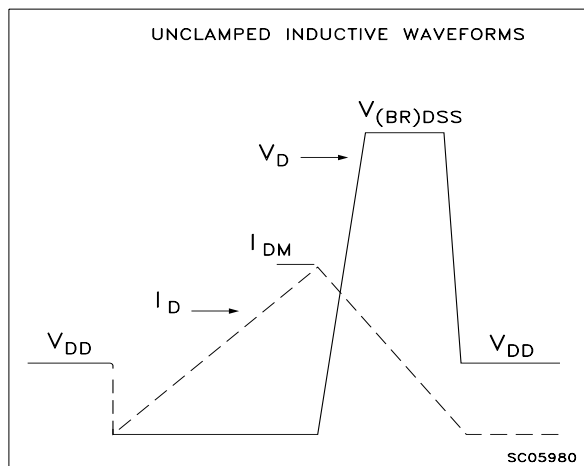


Fig. 3: Switching Times Test Circuits For Resistive Load

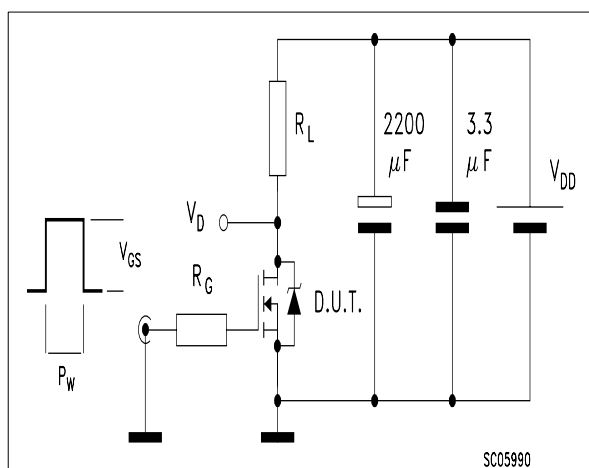


Fig. 4: Gate Charge test Circuit

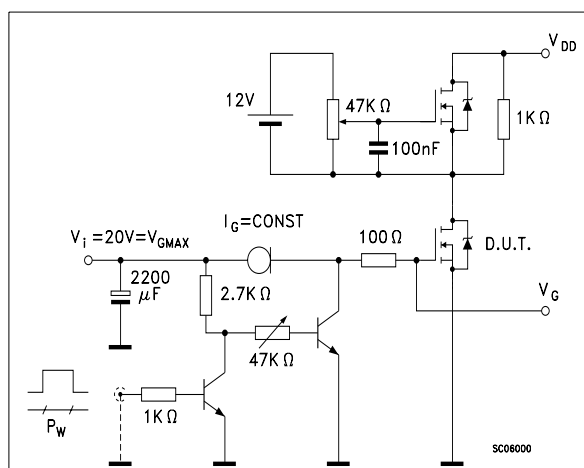
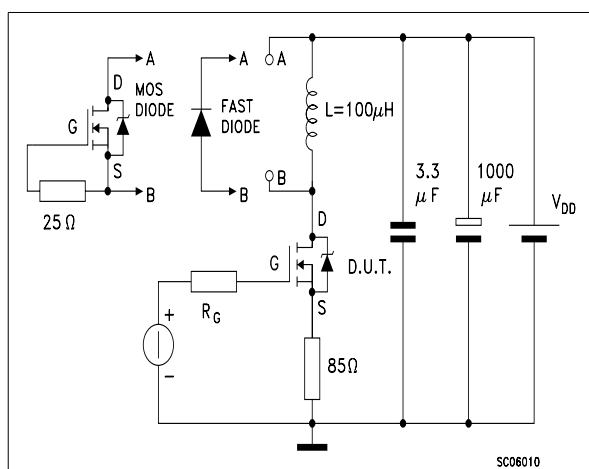
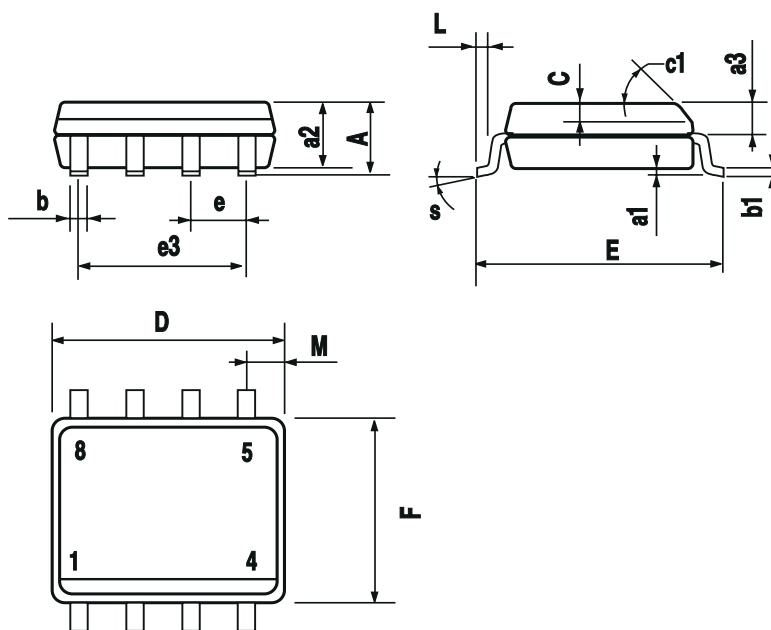


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



SO-8 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.25	0.003		0.009
a2			1.65			0.064
a3	0.65		0.85	0.025		0.033
b	0.35		0.48	0.013		0.018
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.019
c1	45 (typ.)					
D	4.8		5.0	0.188		0.196
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.14		0.157
L	0.4		1.27	0.015		0.050
M			0.6			0.023
S	8 (max.)					



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